



安徽富信半导体科技有限公司

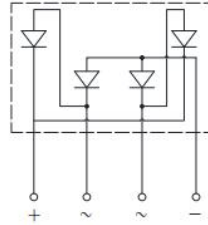
ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

GBJ25005-GBJ2510

Bridge Rectifier Diode 整流桥

■ Features 特点

Glass passivated chip junction 玻璃钝化结
 High surge current capability 高浪涌电流能力
 Ideal for PCB 适用于印刷电路板
 Solder dip 275°C 7S 焊接 275 度 7 秒内
 Package 封装: GBJ



■ Maximum Rating 最大额定值

($T_A=25^\circ\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	GBJ 25005	GBJ 2501	GBJ 2502	GBJ 2504	GBJ 2506	GBJ 2508	GBJ 2510	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	$V_{R(DC)}$	50	100	200	400	600	800	1000	V
Forward Rectified Current 正向整流电流	I_F	25 (With 300X300X1.6mm Heat sink 带散热)							A
Forward Rectified Current 正向整流电流	I_F	4.2 ($T_C=100^\circ\text{C}$ Without Heat sink 不带散热)							A
Peak Surge Current 峰值浪涌电流	I_{FSM}	350							A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	18							$^\circ\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	150 $^\circ\text{C}$, -55to+150 $^\circ\text{C}$							

■ Electrical Characteristics 电特性

($T_A=25^\circ\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F		1.05		V	$I_F=12.5\text{A}$
Reverse Current($T_A=25^\circ\text{C}$) 反向电流($T_A=125^\circ\text{C}$)	I_R			10 500	μA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_D		85		pF	$V_R=4\text{V}, f=1\text{MHz}$

Typical Characteristic Curve 典型特性曲线

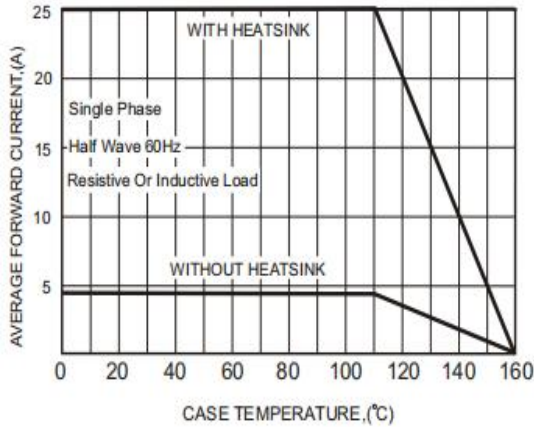


Figure 1: Forward Current Derating Curve

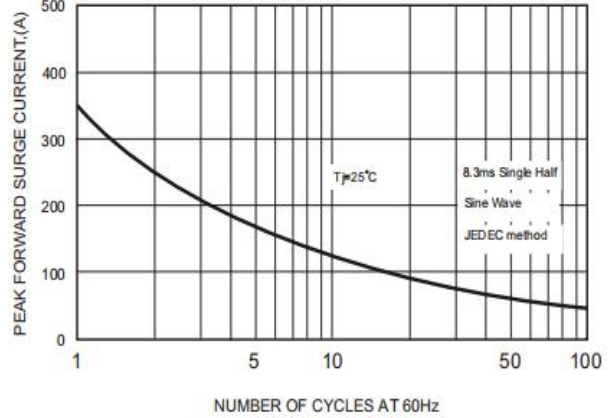


Figure 2: Peak Forward Surge Current

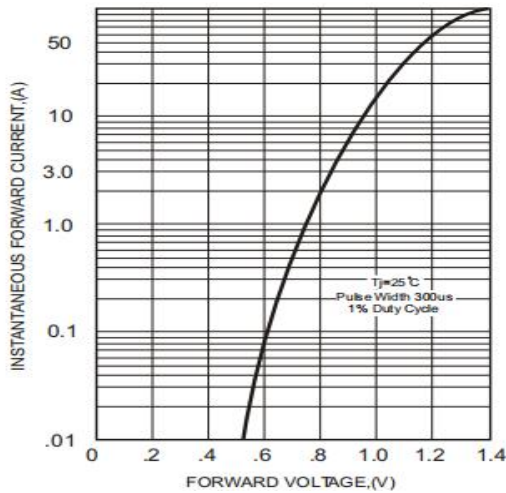


Figure 3: Instantaneous Forward Characteristics

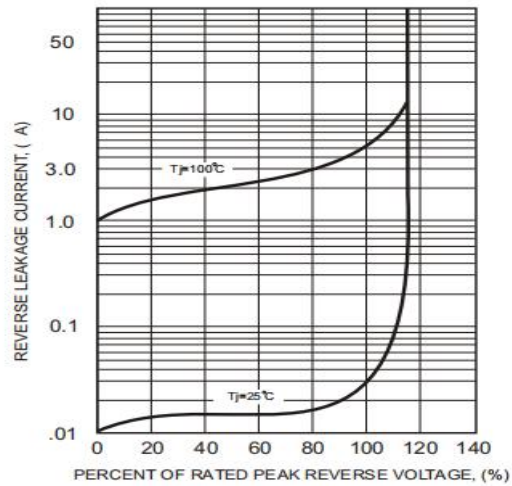


Figure 4: Reverse Leakage Characteristics

Dimension 外形封装尺寸

GBJ Dimensions in inches and (millimeters)

